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October 2016

# ON Semiconductor® FFSP20120A

# Silicon Carbide Schottky Diode 1200 V, 20 A

#### **Features**

- Max Junction Temperature 175 °C
- · Avalanche Rated 200 mJ
- · High Surge Current Capacity
- · Positive Temperature Coefficient
- · Ease of Paralleling
- No Reverse Recovery / No Forward Recovery

#### **Applications**

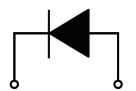
- · General Purpose
- · SMPS, Solar Inverter, UPS
- · Power Switching Circuits

#### **Description**

Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size and cost.



1. Cathode 2. Anode



1. Cathode 2. Anode

### Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted.

Symbol	Parameter	Ratings	Unit	
$V_{RRM}$	Peak Repetitive Reverse Voltage		1200	V
E <sub>AS</sub>	Single Pulse Avalanche Energy (Note 1)		200	mJ
I <sub>F</sub>	Continuous Rectified Forward Current @ T <sub>C</sub> < 148 °C		20	Α
I <sub>F, Max</sub>	Non-Repetitive Peak Forward Surge Current	T <sub>C</sub> = 25 °C, 10 μs	1190	Α
		T <sub>C</sub> = 150 °C, 10 μs	990	Α
I <sub>F,SM</sub>	Non-RepetitiveForwardSurgeCurrent	Half-Sine Pulse, t <sub>p</sub> = 8.3 ms	135	Α
I <sub>F,RM</sub>	Repetitive Forward Surge Current	Half-Sine Pulse, t <sub>p</sub> = 8.3 ms	74	Α
Ptot	Power Dissipation	T <sub>C</sub> = 25 °C	340	W
	Fower Dissipation	T <sub>C</sub> = 150 °C	57	W
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range		-55 to +175	°C

#### **Thermal Characteristics**

Symbol	Parameter	Ratings	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.44	°C/W

# **Package Marking and Ordering Information**

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FFSP20120A	FFSP20120A	TO-220-2L	Tube	N/A	N/A	50 units

#### **Electrical Characteristics** $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
V <sub>F</sub>	Forward Voltage	$I_F = 20 \text{ A}, T_C = 25  ^{\circ}\text{C}$	-	1.45	1.75	V
		I <sub>F</sub> = 20 A, T <sub>C</sub> = 125 °C	-	1.7	2	
		I <sub>F</sub> = 20 A, T <sub>C</sub> = 175 °C	-	2	2.4	
I <sub>R</sub>	Reverse Current	VR = 1200 V, T <sub>C</sub> = 25 °C	-	-	200	
		VR = 1200 V, T <sub>C</sub> = 125 °C	-	-	300	μΑ
		VR = 1200 V, T <sub>C</sub> = 175 °C	-	-	400	1
$Q_C$	Total Capacitive Charge	V = 800 V	-	120	-	nC
С	Total Capacitance	V <sub>R</sub> = 1 V, f = 100 kHz	-	1220	-	
		$V_R = 400 \text{ V}, f = 100 \text{ kHz}$	-	111	-	pF
		$V_R = 800 \text{ V}, f = 100 \text{ kHz}$	-	88	-	

## **Typical Characteristics** $T_J = 25$ °C unless otherwise noted.

Figure 1. Forward Characteristics

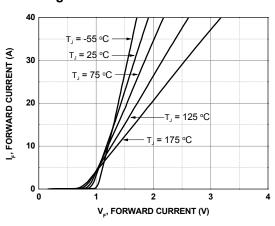


Figure 2. Reverse Characteristics

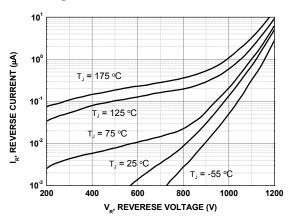


Figure 3. Reverse Characteristics

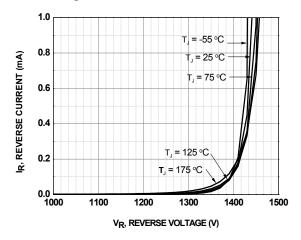
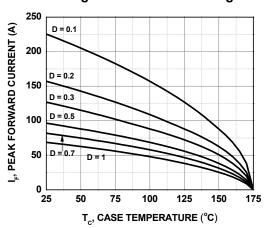


Figure 4. Current Derating



Notes: 1: EAS of 200 mJ is based on starting  $T_J$  = 25 °C, L = 0.5 mH,  $I_{AS}$  = 29 A, V = 150 V.

### **Typical Characteristics** $T_J = 25$ °C unless otherwise noted.

Figure 5. Power Derating

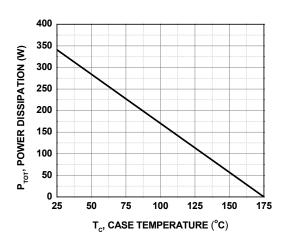


Figure 6. Capacitive Charge vs. Reverse Voltage

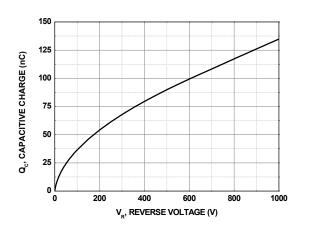


Figure 7. Capacitance vs. Reverse Voltage

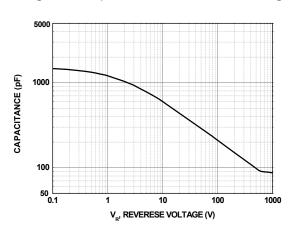


Figure 8. Capacitance Stored Energy

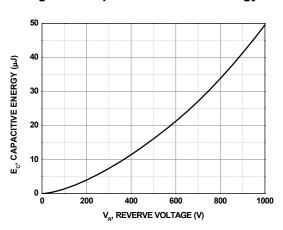
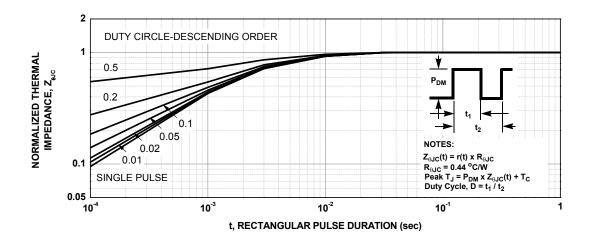
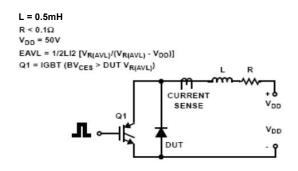


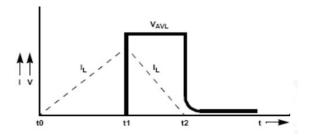
Figure 9. Junction-to-Case Transient Thermal Response Curve

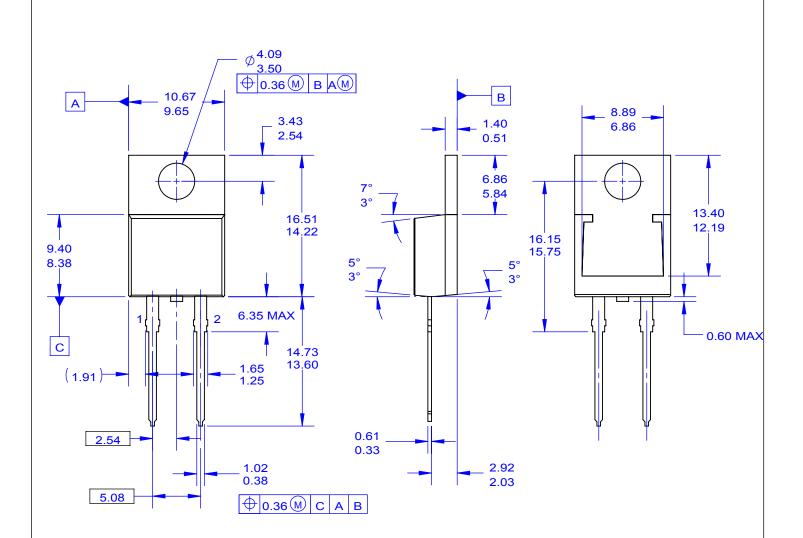


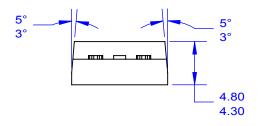
### **Test Circuit and Waveforms**

Figure 10. Unclamped Inductive Switching Test Circuit & Waveform











#### **NOTES**:

- A. PACKAGE REFERENCE: JEDEC TO220,ISSUE K, VARIATION AC,DATED APRIL 2002.
- B. ALL DIMENSIONS ARE IN MILLIMETERS.
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